

# STARPOWER

SEMICONDUCTOR

## IGBT

### GD600HFT65C6S

**Molding Type Module****650V/600A 2 in one-package**

#### General Description

STARPOWER IGBT Power Module provides ultra low conduction loss as well as short circuit ruggedness. They are designed for the applications such as general inverters and UPS.

#### Features

- Low  $V_{CE(sat)}$  Trench IGBT technology
- Low switching losses
- 10 $\mu$ s short circuit capability
- $V_{CE(sat)}$  with positive temperature coefficient
- Maximum junction temperature 175°C
- Low inductance case
- Fast & soft reverse recovery anti-parallel FWD
- Isolated copper pinfin baseplate using DBC technology



#### Typical Applications

- Inverter for motor drive
- AC and DC servo drive amplifier
- Uninterruptible power supply

**IGBT-inverter**  $T_C=25^{\circ}\text{C}$  unless otherwise noted**Maximum Rated Values**

| Symbol    | Description                                                                | GD600HFT65C6S | Unit |
|-----------|----------------------------------------------------------------------------|---------------|------|
| $V_{CES}$ | Collector-Emitter Voltage @ $T_j=25^{\circ}\text{C}$                       | 650           | V    |
| $V_{GES}$ | Gate-Emitter Voltage @ $T_j=25^{\circ}\text{C}$                            | $\pm 20$      | V    |
| $I_C$     | Collector Current @ $T_C=25^{\circ}\text{C}$<br>@ $T_C=55^{\circ}\text{C}$ | 700<br>600    | A    |
| $I_{CM}$  | Pulsed Collector Current $t_p=1\text{ms}$                                  | 1200          | A    |
| $P_{tot}$ | Total Power Dissipation @ $T_j=175^{\circ}\text{C}$                        | 1648          | W    |

**Off Characteristics**

| Symbol        | Parameter                           | Test Conditions                                                 | Min. | Typ. | Max. | Unit |
|---------------|-------------------------------------|-----------------------------------------------------------------|------|------|------|------|
| $V_{(BR)CES}$ | Collector-Emitter Breakdown Voltage | $T_j=25^{\circ}\text{C}$                                        | 650  |      |      | V    |
| $I_{CES}$     | Collector Cut-Off Current           | $V_{CE}=V_{CES}, V_{GE}=0\text{V},$<br>$T_j=25^{\circ}\text{C}$ |      |      | 5.0  | mA   |
| $I_{GES}$     | Gate-Emitter Leakage Current        | $V_{GE}=V_{GES}, V_{CE}=0\text{V},$<br>$T_j=25^{\circ}\text{C}$ |      |      | 400  | nA   |

**On Characteristics**

| Symbol        | Parameter                               | Test Conditions                                                    | Min. | Typ. | Max. | Unit |
|---------------|-----------------------------------------|--------------------------------------------------------------------|------|------|------|------|
| $V_{GE(th)}$  | Gate-Emitter Threshold Voltage          | $I_C=9.6\text{mA}, V_{CE}=V_{GE},$<br>$T_j=25^{\circ}\text{C}$     | 5.1  | 5.8  | 6.4  | V    |
| $V_{CE(sat)}$ | Collector to Emitter Saturation Voltage | $I_C=600\text{A}, V_{GE}=15\text{V},$<br>$T_j=25^{\circ}\text{C}$  |      | 1.45 | 1.75 | V    |
|               |                                         | $I_C=600\text{A}, V_{GE}=15\text{V},$<br>$T_j=150^{\circ}\text{C}$ |      | 1.70 |      |      |

**Switching Characteristics**

| Symbol       | Parameter                    | Test Conditions                                                                          | Min. | Typ. | Max. | Unit     |
|--------------|------------------------------|------------------------------------------------------------------------------------------|------|------|------|----------|
| $t_{d(on)}$  | Turn-On Delay Time           | $V_{CC}=300V, I_C=600A,$<br>$R_G=2.4\Omega, V_{GE}=\pm 15V,$<br>$T_j=25^\circ C$         |      | 98   |      | ns       |
| $t_r$        | Rise Time                    |                                                                                          |      | 91   |      | ns       |
| $t_{d(off)}$ | Turn-Off Delay Time          |                                                                                          |      | 675  |      | ns       |
| $t_f$        | Fall Time                    |                                                                                          |      | 71   |      | ns       |
| $E_{on}$     | Turn-On Switching Loss       |                                                                                          |      | 8.92 |      | mJ       |
| $E_{off}$    | Turn-Off Switching Loss      |                                                                                          |      | 21.6 |      | mJ       |
| $t_{d(on)}$  | Turn-On Delay Time           | $V_{CC}=300V, I_C=600A,$<br>$R_G=2.4\Omega, V_{GE}=\pm 15V,$<br>$T_j=150^\circ C$        |      | 119  |      | ns       |
| $t_r$        | Rise Time                    |                                                                                          |      | 99   |      | ns       |
| $t_{d(off)}$ | Turn-Off Delay Time          |                                                                                          |      | 728  |      | ns       |
| $t_f$        | Fall Time                    |                                                                                          |      | 75   |      | ns       |
| $E_{on}$     | Turn-On Switching Loss       |                                                                                          |      | 10.4 |      | mJ       |
| $E_{off}$    | Turn-Off Switching Loss      |                                                                                          |      | 26.5 |      | mJ       |
| $C_{ies}$    | Input Capacitance            | $V_{CE}=25V, f=1Mhz,$<br>$V_{GE}=0V$                                                     |      | 37.0 |      | nF       |
| $C_{res}$    | Reverse Transfer Capacitance |                                                                                          |      | 1.10 |      | nF       |
| $Q_G$        | Gate Charge                  | $V_{CC}=300V, I_C=600A,$<br>$V_{GE}=-15 \dots +15V$                                      |      | 6.50 |      | $\mu C$  |
| $R_{Gint}$   | Internal Gate Resister       |                                                                                          |      | 0.67 |      | $\Omega$ |
| $I_{SC}$     | SC Data                      | $t_p \leq 6\mu s, V_{GE}=15V,$<br>$T_j=150^\circ C, V_{CC}=360V,$<br>$V_{CEM} \leq 650V$ |      | 3000 |      | A        |

**Diode-inverter**  $T_C=25^\circ C$  unless otherwise noted**Maximum Rated Values**

| Symbol    | Description                                        | GD600HFT65C6S | Unit |
|-----------|----------------------------------------------------|---------------|------|
| $V_{RRM}$ | Repetitive Peak Reverse Voltage @ $T_j=25^\circ C$ | 650           | V    |
| $I_F$     | DC Forward Current                                 | 600           | A    |
| $I_{FRM}$ | Repetitive Peak Forward Current $t_p=1ms$          | 1200          | A    |

**Characteristics Values**

| Symbol           | Parameter                     | Test Conditions                                                                                  |                      | Min. | Typ. | Max. | Unit |
|------------------|-------------------------------|--------------------------------------------------------------------------------------------------|----------------------|------|------|------|------|
| V <sub>F</sub>   | Diode Forward Voltage         | I <sub>F</sub> =600A,<br>V <sub>GE</sub> =0V                                                     | T <sub>j</sub> =25℃  |      | 1.55 | 1.95 | V    |
|                  |                               |                                                                                                  | T <sub>j</sub> =150℃ |      | 1.45 |      |      |
| Q <sub>r</sub>   | Recovered Charge              | I <sub>F</sub> =600A,<br>V <sub>R</sub> =300V,<br>R <sub>G</sub> =2.4Ω,<br>V <sub>GE</sub> =-15V | T <sub>j</sub> =25℃  |      | 16.8 |      | μC   |
|                  |                               |                                                                                                  | T <sub>j</sub> =150℃ |      | 42.1 |      |      |
| I <sub>RM</sub>  | Peak Reverse Recovery Current |                                                                                                  | T <sub>j</sub> =25℃  |      | 204  |      | A    |
|                  |                               |                                                                                                  | T <sub>j</sub> =150℃ |      | 333  |      |      |
| E <sub>rec</sub> | Reverse Recovery Energy       |                                                                                                  | T <sub>j</sub> =25℃  |      | 4.02 |      | mJ   |
|                  |                               |                                                                                                  | T <sub>j</sub> =150℃ |      | 10.4 |      |      |

**Electrical Characteristics of NTC**  $T_C=25^{\circ}\text{C}$  unless otherwise noted

| Symbol       | Parameter              | Test Conditions                                | Min. | Typ. | Max. | Unit       |
|--------------|------------------------|------------------------------------------------|------|------|------|------------|
| $R_{25}$     | Rated Resistance       |                                                |      | 5.0  |      | k $\Omega$ |
| $\Delta R/R$ | Deviation of $R_{100}$ | $R_{100}=493.3\Omega$                          | -5   |      | 5    | %          |
| $P_{25}$     | Power Dissipation      |                                                |      |      | 20.0 | mW         |
| $B_{25/50}$  | B-value                | $R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15K))]$ |      | 3375 |      | K          |

**IGBT Module**

| Symbol          | Parameter                                                              | Min.       | Typ.  | Max.           | Unit               |
|-----------------|------------------------------------------------------------------------|------------|-------|----------------|--------------------|
| $V_{ISO}$       | Isolation Voltage RMS, $f=50\text{Hz}$ , $t=1\text{min}$               | 2500       |       |                | V                  |
| $L_{CE}$        | Stray Inductance                                                       |            | 20    |                | nH                 |
| $R_{CC'+EE'}$   | Module Lead Resistance, Terminal to Chip<br>@ $T_C=25^{\circ}\text{C}$ |            | 1.10  |                | m $\Omega$         |
| $R_{\theta JC}$ | Junction-to-Case (per IGBT)<br>Junction-to-Case (per Diode)            |            |       | 0.091<br>0.152 | K/W                |
| $R_{\theta CS}$ | Case-to-Sink (Conductive grease applied)                               |            | 0.009 |                | K/W                |
| $T_{jmax}$      | Maximum Junction Temperature                                           |            |       | 175            | $^{\circ}\text{C}$ |
| $T_{jop}$       | Operating Junction Temperature                                         | -40        |       | 150            | $^{\circ}\text{C}$ |
| $T_{stg}$       | Storage Temperature Range                                              | -40        |       | 125            | $^{\circ}\text{C}$ |
| M               | Terminal Connection Torque, Screw M5<br>Mounting Torque, Screw M6      | 3.0<br>3.0 |       | 6.0<br>6.0     | N.m                |
| G               | Weight of Module                                                       |            | 350   |                | g                  |

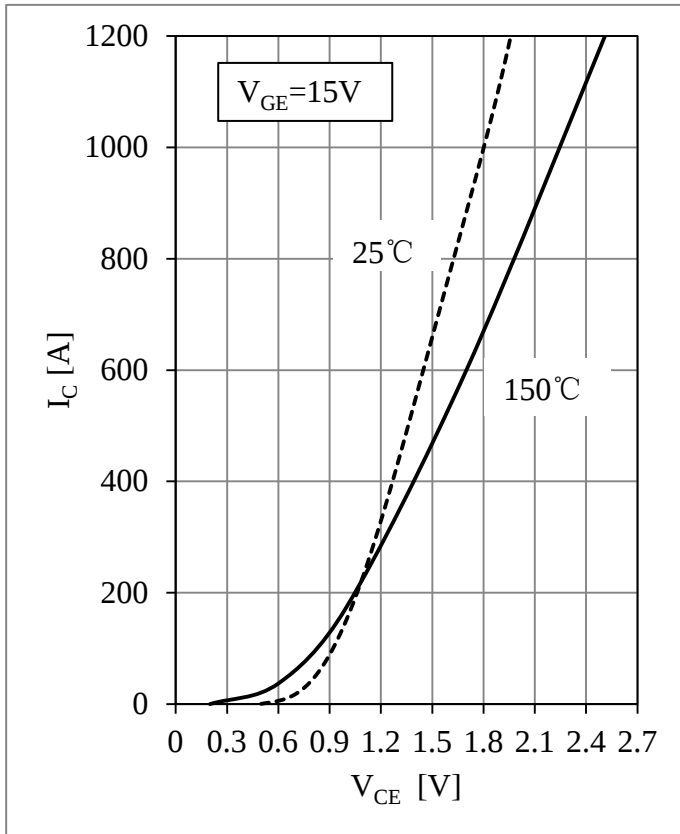


Fig 1. IGBT-inverter Output Characteristics

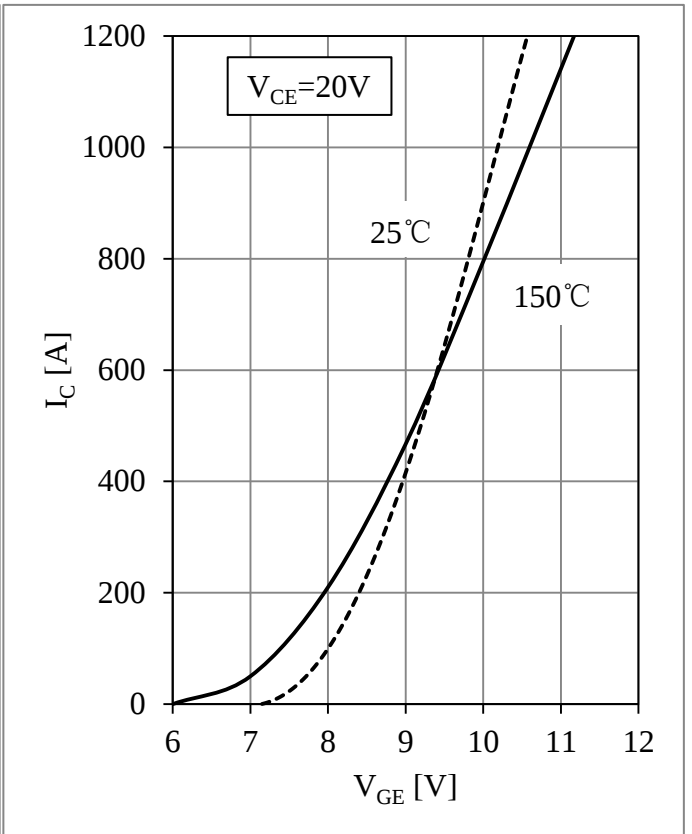
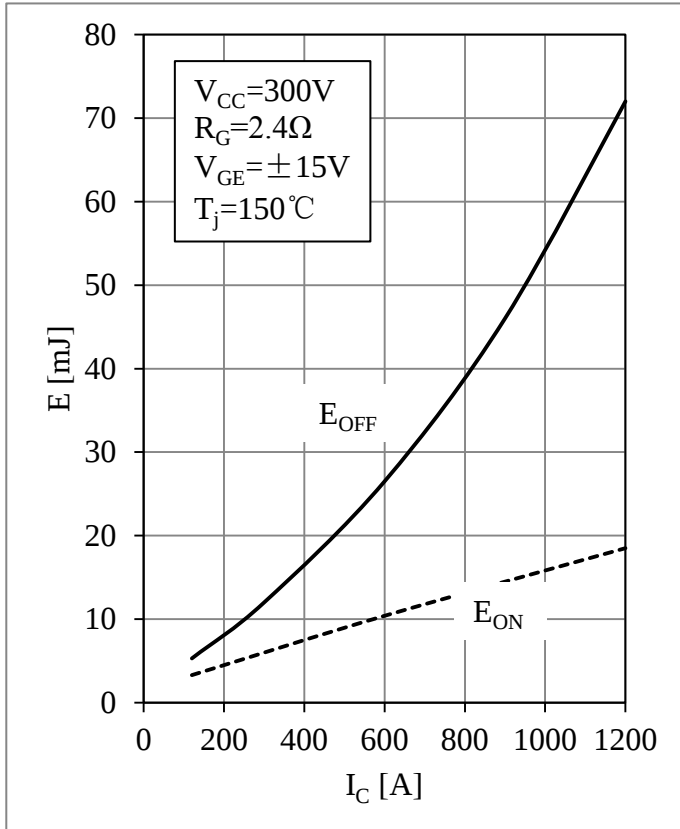
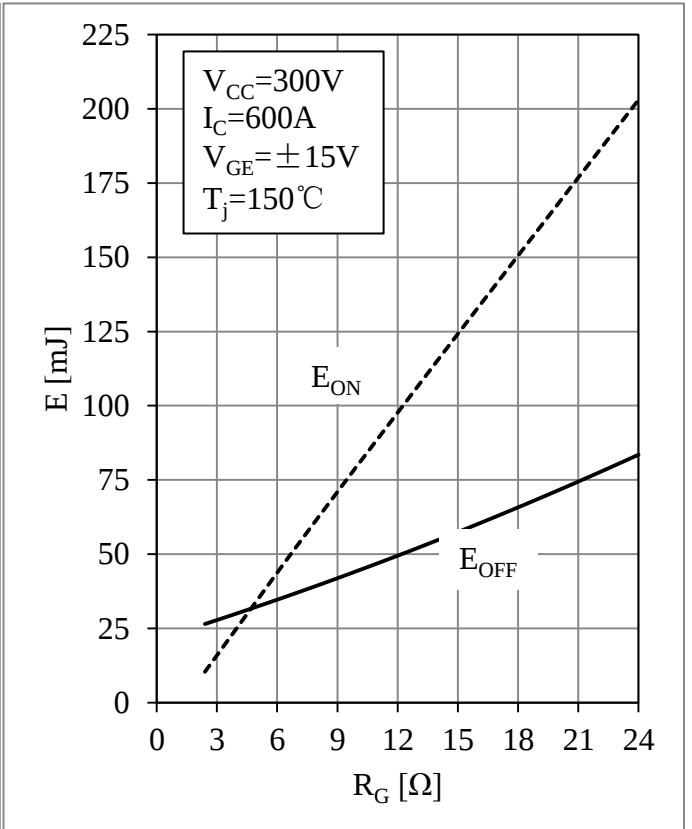


Fig 2. IGBT-inverter Transfer Characteristics

Fig 3. IGBT-inverter Switching Loss vs.  $I_C$ Fig 4. IGBT-inverter Switching Loss vs.  $R_G$

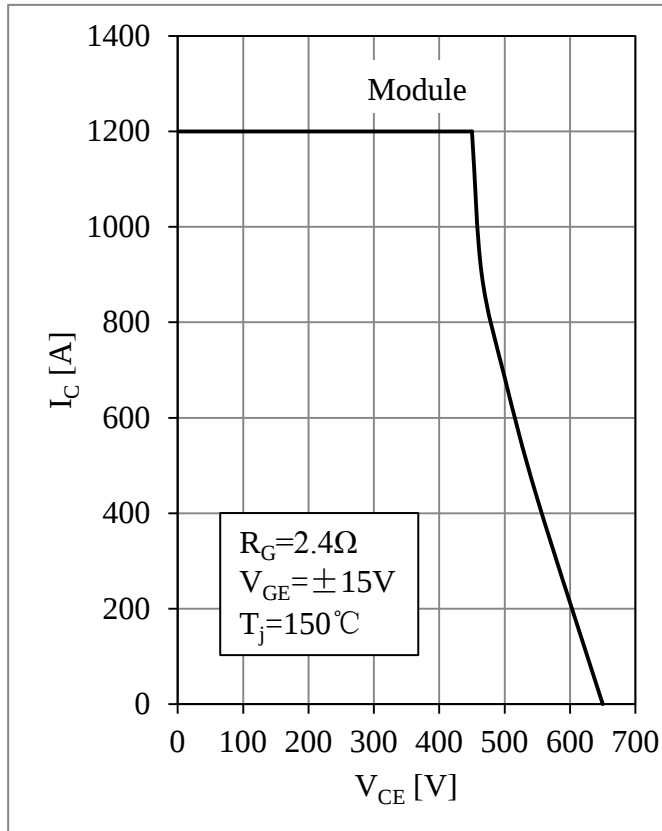


Fig 5. IGBT-inverter RBSOA

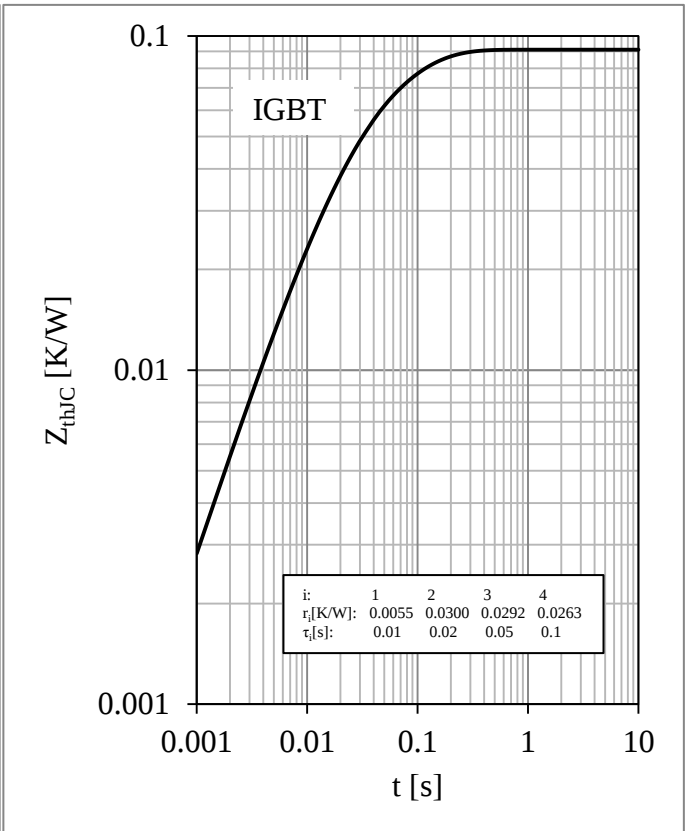


Fig 6. IGBT-inverter Transient Thermal Impedance

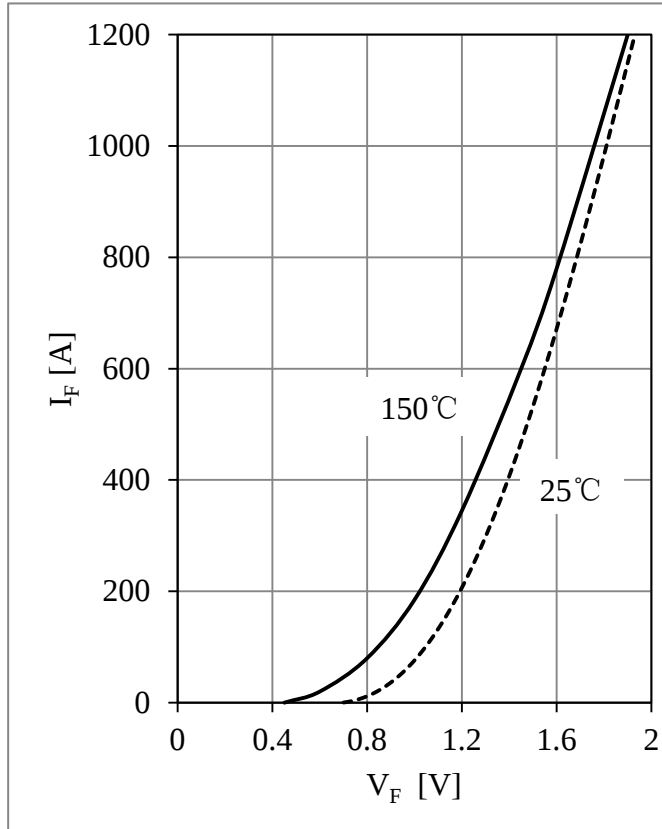
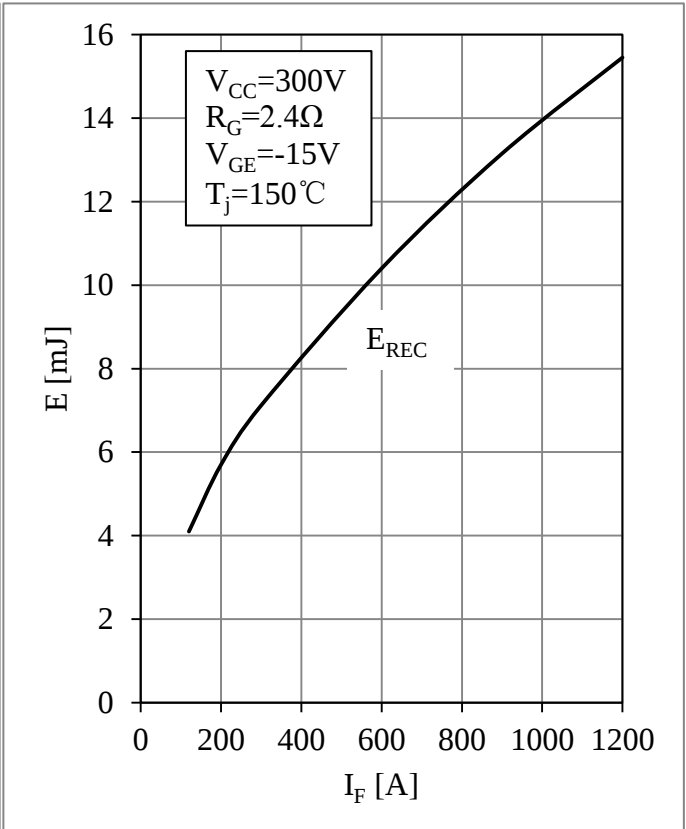


Fig 7. Diode-inverter Forward Characteristics

Fig 8. Diode-inverter Switching Loss vs.  $I_F$

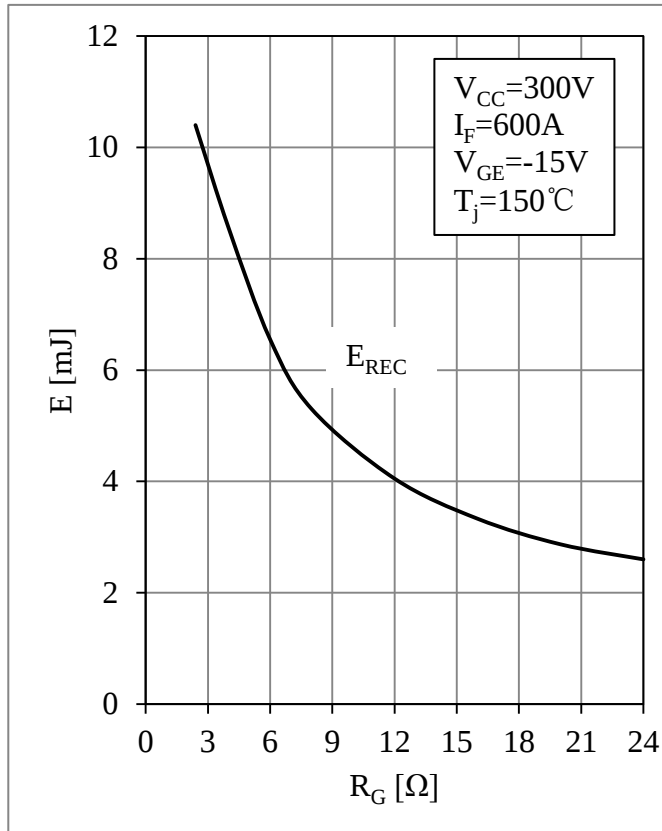
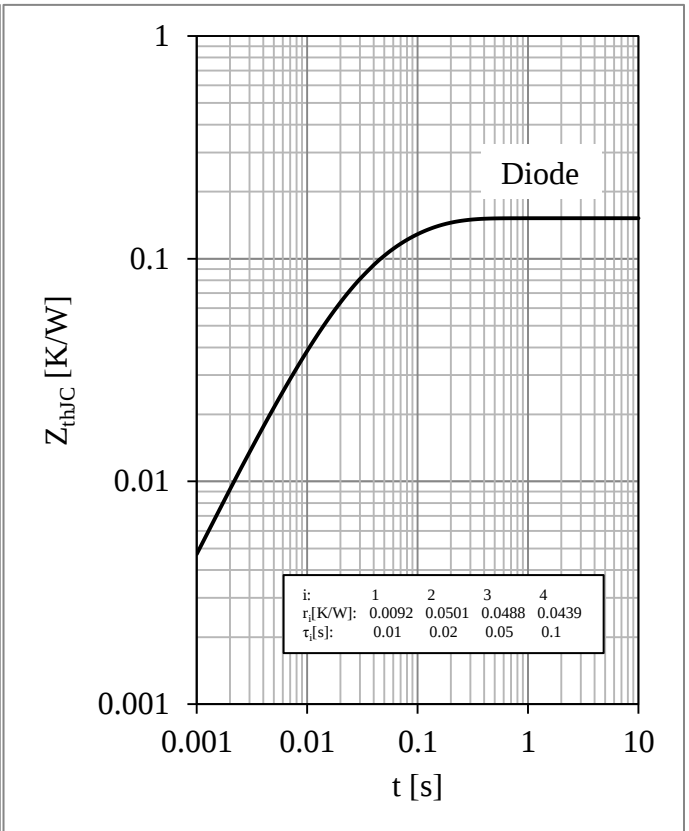
Fig 9. Diode-inverter Switching Loss vs.  $R_G$ 

Fig 10. Diode-inverter Transient Thermal Impedance

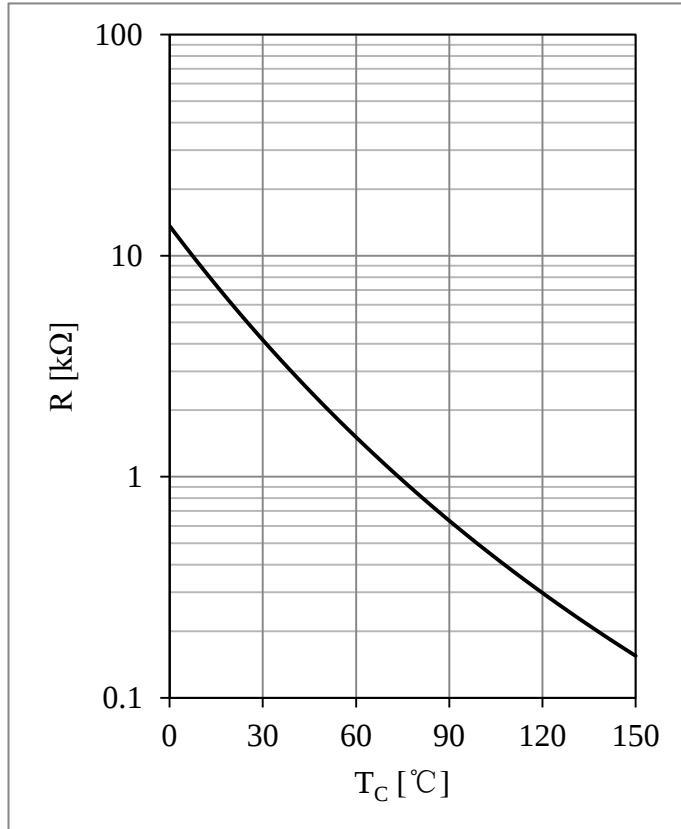


Fig 11. NTC Temperature Characteristic



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